1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

- · Fully automotive qualified to beyond AEC-Q101:
 - -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package
 - Designed for smaller footprint and improved power density over older wire bond packages such as D²PAK for today's space constrained high power automotive applications
 - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
 - Increased maximum current capability and excellent current spreading
 - Improved R_{DSon}
 - Low source inductance
 - Low thermal resistance R_{th}
- LFPAK Gull Wing leads:
 - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
 - Reduced cell pitch and superjunction platform enables lower R_{DSon} in the same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs

3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- LED lighting
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	425	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	375	W



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Tj	junction temperature			-55	-	175	°C
Static characte	ristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 11		0.43	0.62	0.7	mΩ
Dynamic chara	cteristics						
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	25	50	nC
Source-drain diode							
Q _r	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	[2]	-	74	-	nC

^{[1] 425}A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D ₋
2	S	source		
3	S	source		G_(F)
4	S	source		mbb076 S
mb	D	mounting base; connected to drain	LFPAK88 (SOT1235)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7S0R7-40H	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7S0R7-40H	7S0R740H

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	40	V

^[2] includes capacitive recovery

Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	375	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	425	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	1983	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	[2]	-	500	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1983	Α
Avalanche ru	uggedness			'	•	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 120 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	940	mJ

- [1] 425A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.
- [2] 500A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

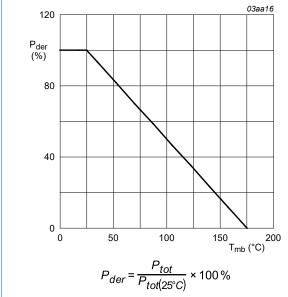
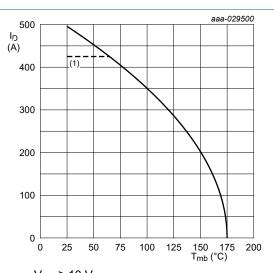


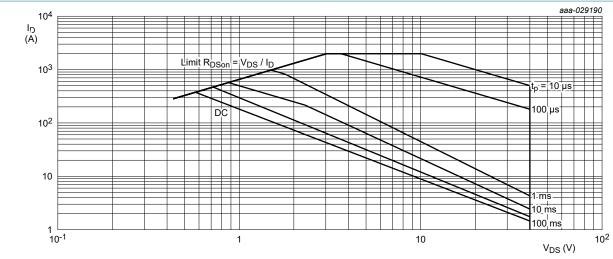
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ (1) 425A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

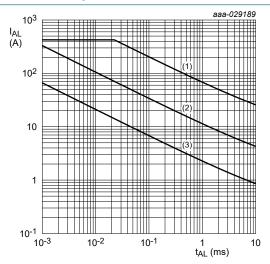
Fig. 2. Continuous drain current as a function of mounting base temperature

N-channel 40 V, 0.7 $m\Omega$ standard level MOSFET in LFPAK88



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}} = 25 \text{ °C}$; (2) $T_{j \text{ (init)}} = 150 \text{ °C}$; (3) Repetitive Avalanche

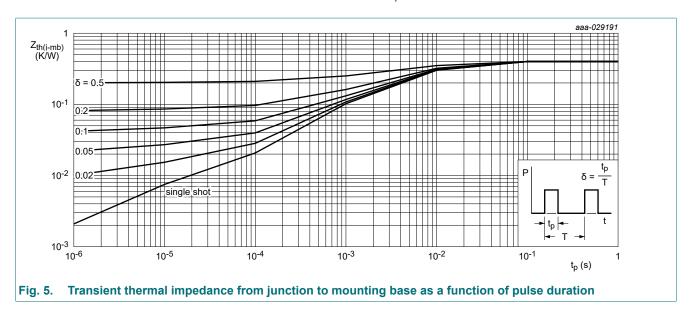
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	0.35	0.4	K/W

N-channel 40 V, 0.7 m Ω standard level MOSFET in LFPAK88



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.3	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.86	2.3	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	10	25	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	614	1500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11	0.43	0.62	0.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 105 °C;$ Fig. 12	0.61	0.9	1.11	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 125 °C; Fig. 12	0.68	1	1.23	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ Fig. 12	0.85	1.23	1.53	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.5	1.2	3	Ω
Dynamic ch	naracteristics		1			_
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	144	202	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	40	60	nC
Q_{GD}	gate-drain charge	1	-	25	50	nC

N-channel 40 V, 0.7 m Ω standard level MOSFET in LFPAK88

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;		-	11228	15719	рF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	2363	3308	pF
C _{rss}	reverse transfer capacitance			-	415	913	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;		-	35	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	30	-	ns
t _{d(off)}	turn-off delay time			-	94	-	ns
t _f	fall time			-	41	-	ns
Source-dra	ain diode	,	'				
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.75	1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	53	-	ns
Q _r	recovered charge	V _{DS} = 20 V	[1]	-	74	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C		-	0.79	-	
		I_S = 25 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_i = 25 °C		-	0.73	-	

[1] includes capacitive recovery

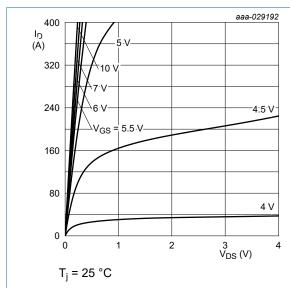


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

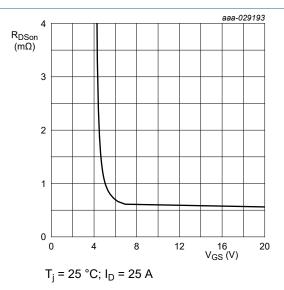


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

N-channel 40 V, 0.7 m Ω standard level MOSFET in LFPAK88

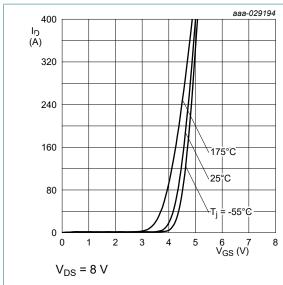


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

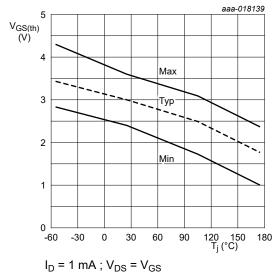


Fig. 10. Gate-source threshold voltage as a function of junction temperature

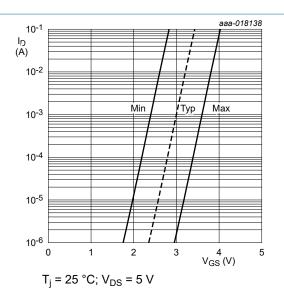


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

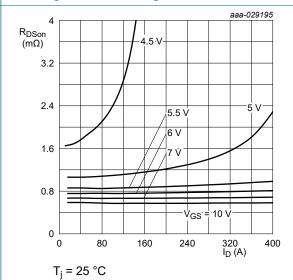


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 40 V, 0.7 m Ω standard level MOSFET in LFPAK88

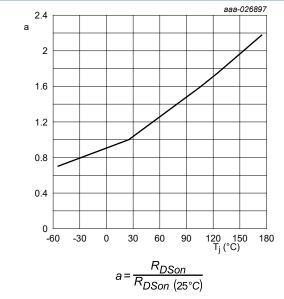


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

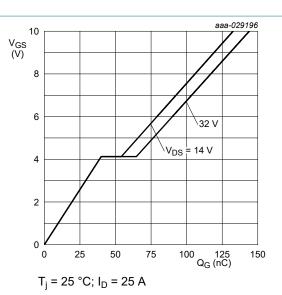


Fig. 13. Gate-source voltage as a function of gate charge; typical values

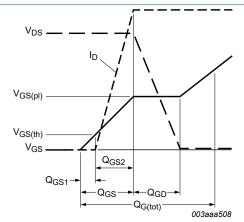
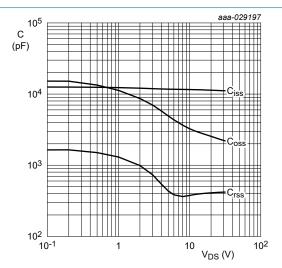


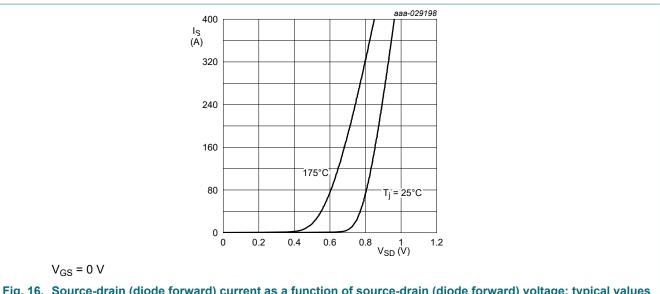
Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

N-channel 40 V, 0.7 m Ω standard level MOSFET in LFPAK88



11. Package outline

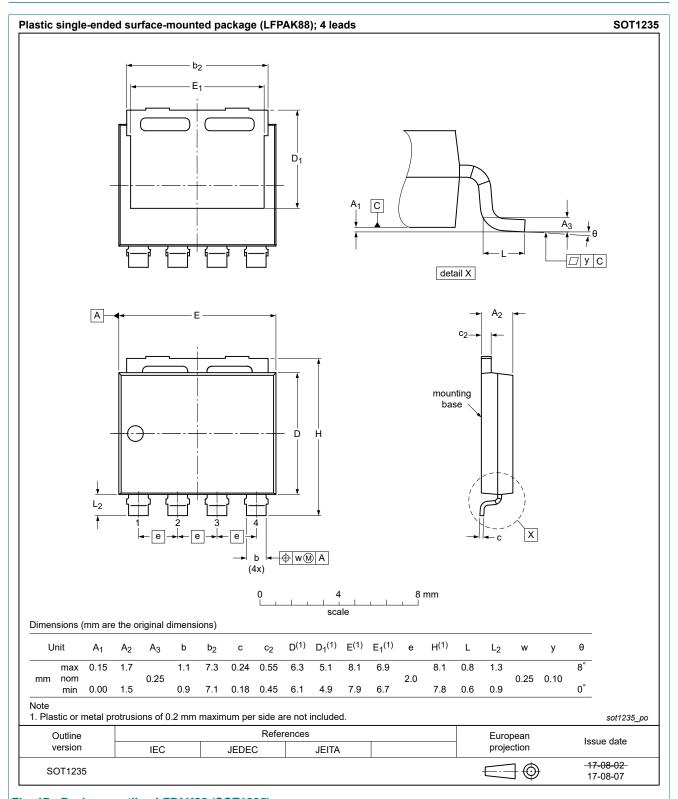
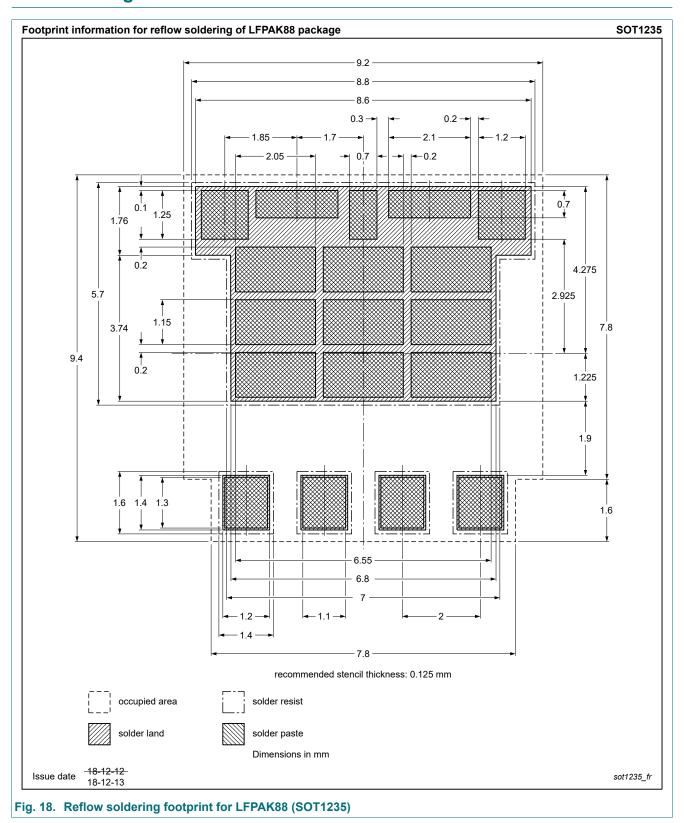


Fig. 17. Package outline LFPAK88 (SOT1235)

12. Soldering



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	2
9. Thermal characteristics	4
10. Characteristics	5
11. Package outline	10
12. Soldering	
13. Legal information	

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